DTCO and Computational Patterning II

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## Contents

ix  Conference Committee

### CURVILINEAR IN COMPUTATIONAL PATTERNING

<table>
<thead>
<tr>
<th>Paper</th>
<th>Title</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 03</td>
<td>Full chip inverse lithography technology mask synthesis for advanced memory manufacturing [12495-1]</td>
</tr>
<tr>
<td>12495 04</td>
<td>Structured assist features in inverse lithography [12495-2]</td>
</tr>
<tr>
<td>12495 05</td>
<td>Curvilinear mask handling in OPC flow [12495-3]</td>
</tr>
<tr>
<td>12495 06</td>
<td>Curvilinear data representation and its impact on file size and lithographic performance [12495-4]</td>
</tr>
</tbody>
</table>

### COMPUTATIONAL PATTERNING I AND HIGH NA EUV

<table>
<thead>
<tr>
<th>Paper</th>
<th>Title</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 08</td>
<td>Improving OPC modeling accuracy with rigorous and compact modeling deformation effects in photoresists [12495-6]</td>
</tr>
<tr>
<td>12495 09</td>
<td>Computational evaluation of critical logical metal layers of pitch 20-24nm and the aberration sensitivity in high NA EUV single patterning [12495-8]</td>
</tr>
<tr>
<td>12495 0A</td>
<td>Application of resolution enhancement techniques at high NA EUV for next generation DRAM patterning [12495-9]</td>
</tr>
<tr>
<td>12495 0B</td>
<td>Evaluation of field stitching optimization for robust manufacturing with high-NA EUVL [12495-10]</td>
</tr>
<tr>
<td>12495 0C</td>
<td>Probability model of bridging defects for random logic via in 3nm double patterning technology at 0.33 NA [12495-68]</td>
</tr>
</tbody>
</table>

### INVITED PRESENTATIONS I

<table>
<thead>
<tr>
<th>Paper</th>
<th>Title</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 0D</td>
<td>Direct print EUV patterning of tight pitch metal layers for Intel 18A process technology node (Invited Paper) [12495-11]</td>
</tr>
</tbody>
</table>
### INVITED PRESENTATIONS II

<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
<th>Reference</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 0K</td>
<td>EUV full-chip curvilinear mask options for logic via and metal patterning (Invited Paper)</td>
<td>[12495-18]</td>
</tr>
<tr>
<td>12495 0L</td>
<td>Next-generation logic design architecture for vertical-transport nanosheets (Invited Paper)</td>
<td>[12495-20]</td>
</tr>
<tr>
<td>12495 0M</td>
<td>Design-technology co-optimization overview of CFET architecture (Invited Paper)</td>
<td>[12495-21]</td>
</tr>
</tbody>
</table>

### COMPUTATIONAL PATTERNING II

<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
<th>Reference</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 0P</td>
<td>High accuracy OPC modeling for new EUV low-K1 mask technology options</td>
<td>[12495-25]</td>
</tr>
<tr>
<td>12495 0Q</td>
<td>Modeling accuracy and TAT improvements for next generation mask error correction</td>
<td>[12495-26]</td>
</tr>
</tbody>
</table>

### COMPUTATIONAL LITHOGRAPHY: JOINT SESSION WITH 12495 AND 12494

<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
<th>Reference</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 0R</td>
<td>Computational lithography solutions to support EUV high-NA patterning</td>
<td>[12495-27]</td>
</tr>
<tr>
<td>12495 0S</td>
<td>Patterning assessment using 0.33NA EUV single mask for next generation DRAM manufacturing</td>
<td>[12495-28]</td>
</tr>
</tbody>
</table>

### DESIGN FOR MANUFACTURING AND YIELD

<table>
<thead>
<tr>
<th>Session</th>
<th>Title</th>
<th>Reference</th>
</tr>
</thead>
<tbody>
<tr>
<td>12495 0T</td>
<td>IC layouts patterns topological profiling using directional geometrical kernels</td>
<td>[12495-29]</td>
</tr>
<tr>
<td>12495 0U</td>
<td>Methodology development to benchmark power delivery designs in advanced technology nodes</td>
<td>[12495-30]</td>
</tr>
<tr>
<td>12495 0V</td>
<td>Design for manufacturability (DFM) in-design fixing for improving manufacturability aware scoring (MAS)</td>
<td>[12495-31]</td>
</tr>
<tr>
<td>12495 0W</td>
<td>Electrical analysis of a stochastically simulated 2 nm node electrical test structure</td>
<td>[12495-32]</td>
</tr>
<tr>
<td>12495 0X</td>
<td>Scalable hierarchy extraction of repeating structures to enhance full chip mask synthesis</td>
<td>[12495-33]</td>
</tr>
</tbody>
</table>
DTCO AND STCO

12495 0Y  System-level evaluation of 3D power delivery network at 2nm node [12495-34]

12495 0Z  DTCO of sequential and monolithic CFET SRAM [12495-35]

12495 11  Minimizing die fracture in three-dimensional IC advanced packaging wafer thinning process by inserting polyimide patterns [12495-37]

INVITED PRESENTATIONS III: DESIGN FOR TEST AND METROLOGY

12495 15  A holistic approach to zero defect products when wafer fab does not output zero defects (Invited Paper) [12495-41]

12495 16  Voltage contrast evaluation of dual-damascene 28nm-pitch EUV patterning and via overlap (Invited Paper) [12495-42]

12495 17  Design for inspection methodology for fast in-line eBeam defect detection (Invited Paper) [12495-43]

MACHINE LEARNING, DEEP LEARNING, AND AI I

12495 18  Unsupervised ML classification driven process model coverage check [12495-44]

12495 19  Machine learning architecture evaluation for fast and accurate weak point detection [12495-45]

12495 1A  Machine learning applications on 3nm node technology and designs for improving block-level PPA [12495-46]

12495 1B  Automatic generation of representative and diversified pattern samples from a full chip layout [12495-47]

12495 1C  Quantifying process sensitivities for EUV and high-NA using machine learning based analytics [12495-48]

MACHINE LEARNING, DEEP LEARNING, AND AI II

12495 1D  Frequency-informed deep-learning denoising method supporting sub-nm metrology for high NA EUV lithography [12495-49]

12495 1F  Optical proximity correction with the conditional Wasserstein GAN [12495-56]
Design for manufacturability (DFM) physical verification using machine learning [12495-52]

Etch model calibration and usage in OPC flow for curvilinear layouts [12495-53]

**MACHINE LEARNING, DEEP LEARNING, AND AI III**

Evaluation of CNN for fast EUV lithography simulation using iN3 logic mask patterns [12495-55]

**POSTER SESSION**

Cost analysis of device options and scaling boosters below the A14 technology node [12495-59]

Improving FEM wafer review efficiency by introducing different pattern grouping modes [12495-60]

Lithography hotspot detection based on residual network [12495-62]

Constructing layout hierarchy for high-efficiency OPC flow [12495-63]

CPU time prediction using machine learning for post-tapeout flow runs [12495-64]

GPU-accelerated matrix cover algorithm for multiple patterning layout decomposition [12495-65]

Co-optimization of optical and resist models in the OPC modeling process using in-house genetic algorithm [12495-67]

Hybrid deep learning OPC framework with generative adversarial network [12495-69]

Fast and accurate machine learning assisted mask optimization [12495-71]

Design rule manual and DRC code qualification flows empowered by high coverage synthetic layouts generation [12495-72]

Productivity enhancement study: yield, cost, and turn-around-time modeling for EUV and high NA EUV [12495-73]

Design-aware virtual metrology and process recipe recommendation [12495-75]

A geometric model for active contours in inverse lithography [12495-76]

Physical design level PPA evaluation of buried power rail at 2nm node [12495-58]
12495 1Y Lithography hotspot correction on post-OPC layout using generative adversarial networks [12495-57]

12495 1Z Fast and accurate prediction of process variation band with custom kernels extracted from convolutional networks [12495-70]

12495 20 Layout pattern risk assessment in advanced technology node: methodology for pattern clustering and classification [12495-7]

DIGITAL POSTER SESSION

12495 24 Optical proximity correction with PID control through reinforcement learning [12495-24]

12495 25 Thick-mask model based on multi-channel U-Net for EUV lithography [12495-61]
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